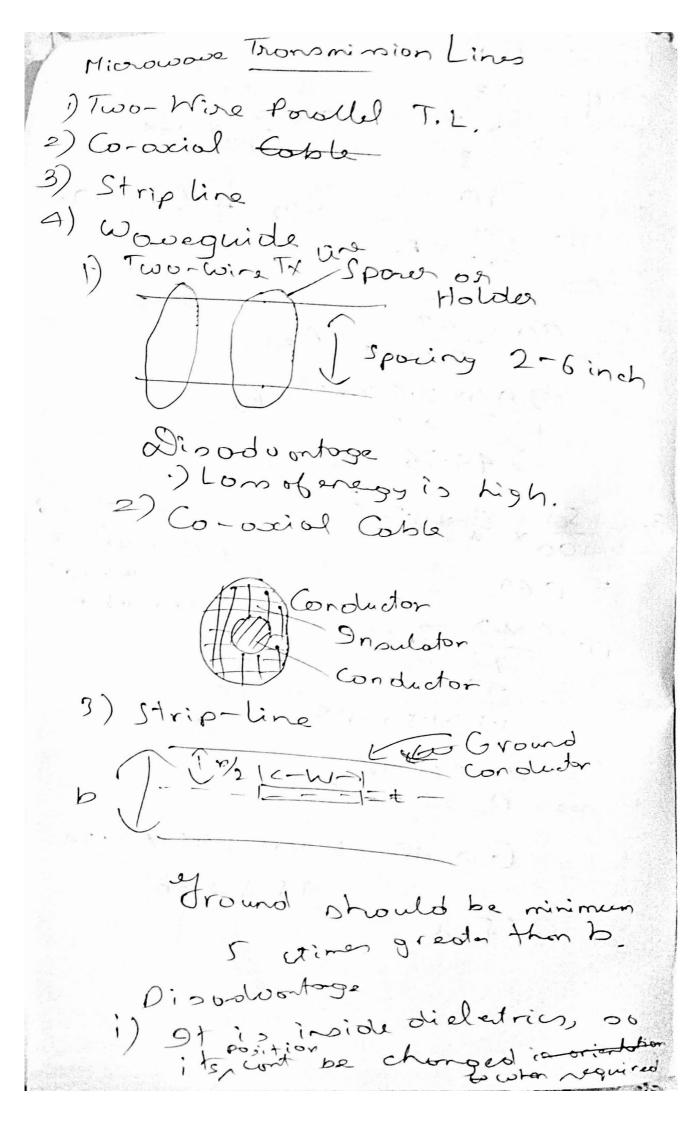
Microwave Integrated Circuits (OF-EC Frequency ronge 300 mH2 to E=hz=hC 300642 Frequency = Sx ×100 ×100 ×100 y - 100 1m 1×100 = 3×10 Oscillator R=PA

 $\frac{1}{\sum_{i=1}^{N} x^{i}} = \frac{1}{\sum_{i=1}^{N} x^{i}} = \frac{1}{\sum_{i=1}^{N}$

MESFET

becouse of metal semiconductor contact, or applying smell voltage, we get high current.

AIC



A) Woveguide L02 V(2) B Load F03 B RA2 LA2 A (02 602 \$ G02 } (2,t)02 (2) R (12 - L 2i(2t)
02 7 8t ~(2+02,t)+ V(2,t) = 0V(2+02),t)-V(2,t)02 i (2,t)R

-ROZi(2,t)-LOZi(d)(2,t -RO2 i(2)+)- Lazidi(2,+) U(z+02,+)+ U(2,+)=0 =)-Ri(2,+)-Lai(z,+)= 24 V(2+02,+)-V(2,+) 02 =) - Ri(2,+) - L di(2,+)= : VG: i(2,+) = i(ig + ic+ ((2+02,t) == ig - ic = i(2,+02,t)i(2,t) =) _U(2+02) G02-2 v'(z+02) (02 = i(2+02)) i(2,+)

=) -V(z+0z,t) 6 - $\partial V(z+0z,t)$ $C = \frac{\partial i(z,t)}{\partial t^2}$ $V(z) = V(z,t) - R(0z) R0z \frac{\partial i(z,t)}{\partial t}$ $V(z,t) - R(0z) R0z \frac{\partial i(z,t)}{\partial t}$ $V(z,t) - L0z \frac{\partial i(z,t)}{\partial t} = \frac{1}{2}$ Characteristic Impedence.

$$\frac{d1}{d2} = +\frac{1}{2^2} \frac{dv}{d^2} - \frac{1}{2^2} \frac{d^2v}{dz^2}$$

A Using binomial (1+0.000001)2 opproximation no Viwl (ziwl+1) Viwc (Eiwc+1) - Vjwl Vjwc (1+ R 2iwl+ $= j\omega\sqrt{lc}\left(1+\frac{R}{2j\omega l}\right)$ 2; wc) 2 [R\= + G\= + i w\[c] - X+jB Colculate shorateistic impedo impedance at high frague frague frequency Zo= VP+jwl G+jwc

[] we ~o - // $\frac{G}{W} \approx 0$ Rate of chonge since wis of phose very high w.nto direction V= (2,+)= V(z,t) = Re Re Ve just e just = cos(wt-BZ) wt-Bz = wonstant Phose velocity velocity $u_p = \frac{ol2}{alt} = \frac{\omega}{B}$ B-WTLC

WP = WTLC

WOLC

TO THE $\omega - \beta \frac{d^2}{d^4} = 0 \rightarrow 0 \rho^2 \frac{\omega}{\beta}$